

Abstract of the Disclosure

A package structure for a semiconductor device comprises a substrate having a main surface and a back surface, a semiconductor chip formed on the main surface of the substrate, a package covering the semiconductor chip, radiation protrude electrodes and connection protrude electrodes. The radiation protrude electrodes are formed on the back surface of the substrate in a chip area where said semiconductor chip is located. Each of the radiation protrude electrodes are formed with a first pitch so that the radiation protrude electrodes make one body joining layer when the package structure is subjected to a heat treatment. The connection protrude electrodes are formed on the back surface of the substrate in a peripheral area of the chip area. Each of the connection protrude electrodes formed with a second pitch which is larger than the first pitch so that the connection protrude electrodes stay individual when the package structure is subjected to a heat treatment.